TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2 S C 2 7 1 2

AUDIO FREQUENCY GENERAL PURPOSE AMPLIFIER APPLICATIONS.

• High Voltage and High Current

: $V_{CEO} = 50V$, $I_{C} = 150mA$ (Max.)

• Excellent hpp Linearity

: $h_{FE} (I_C = 0.1 \text{mA}) / h_{FE} (I_C = 2 \text{mA}) = 0.95 \text{ (Typ.)}$

• High hFE: $hFE = 70 \sim 700$

• Low Noise: NF=1dB (Typ.), 10dB (Max.)

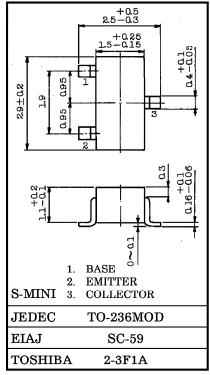
• Complementary to 2SA1162

• Small Package

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	50	V
Emitter-Base Voltage	v_{EBO}	5	V
Collector Current	IC	150	mA
Base Current	$I_{\mathbf{B}}$	30	mA
Collector Power Dissipation	PC	150	mW
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C

Unit in mm



Weight: 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	ICBO	$V_{\rm CB} = 60 \rm V, \ I_{\rm E} = 0$	_	_	0.1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_{C}=0$	_	_	0.1	μ A
DC Current Gain	hFE(Note)	$V_{CE}=6V, I_{C}=2mA$	70	_	700	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_{\rm C} = 100 {\rm mA}, \ I_{\rm B} = 10 {\rm mA}$	_	0.1	0.25	V
Transtion Frequency	$ m f_{T}$	$V_{\rm CE}$ =10V, $I_{\rm C}$ =1mA	80	_	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	2.0	3.5	рF
Noise Figure	NF	$V_{\text{CE}}=6V$, $I_{\text{C}}=0.1\text{mA}$, $f=1\text{kHz}$, $R_{g}=10\text{k}\Omega$	_	1.0	10	dB

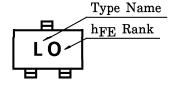
Note: hFE Classification

 $O(O): 70\sim140, Y(Y): 120\sim240, GR(G): 200\sim400,$

BL(L): 350~700

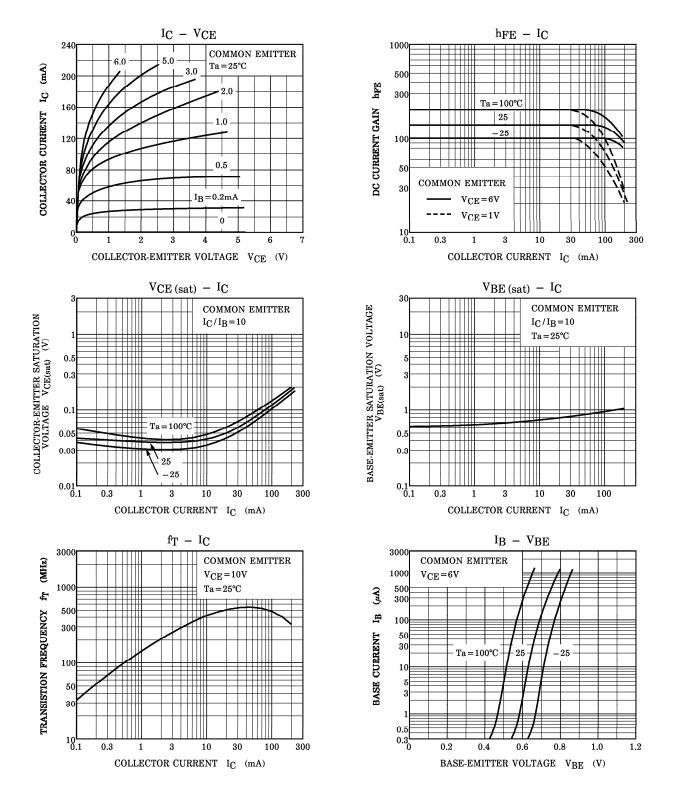
() Marking Symbol

MARKING



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